

## Supporting Information

### Stabilization of organic field-effect transistors by *t*-butyl groups in dibenzotetrathiafulvalene derivatives

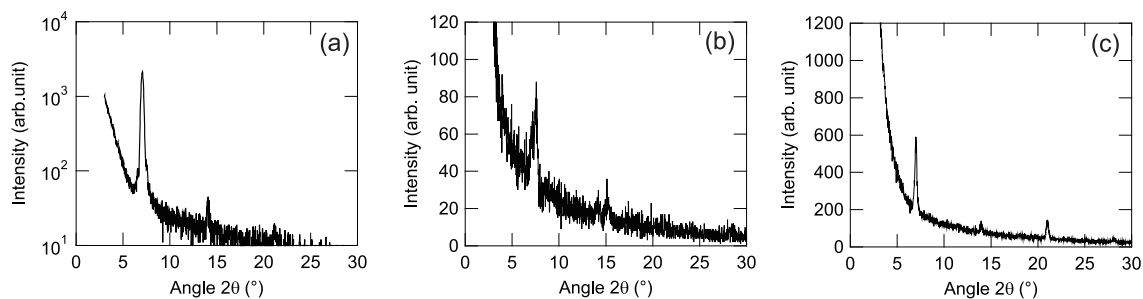
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#### 1. XRD patterns

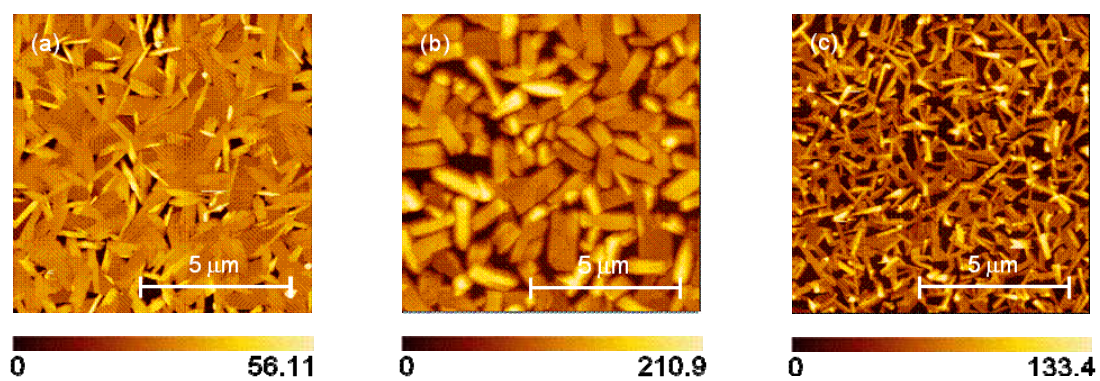
Figure S1 shows XRD patterns, where the  $d$  values are 12.5 Å for **1d**, 11.7 Å for **1e**, and 12.6 Å for **2**. The values for **1d** and **1e** are close to that for **1c**, indicating similar molecular packing, though the peak is unclear in **1e**. The  $d$  value for **2** does not simply correspond to the lattice constants of the single crystal (Table 2).



**Figure S1.** XRD patterns for the thin films of (a) **1d**, (b) **1e**, and (c) **2**, deposited on SiO<sub>2</sub>.

## 2. AFM images

Figure S2 shows AFM images for **1d**, **1e**, and **2**. **1d** and **1e** consist of needle-like and block-like crystals, respectively. **2** consists of relatively fine crystals, and shows comparatively large spaces between the crystals.



**Figure S2.** AFM images for the thin films (a) **1d**, (b) **1e**, and (c) **2**, deposited on SiO<sub>2</sub> deposited on SiO<sub>2</sub>.